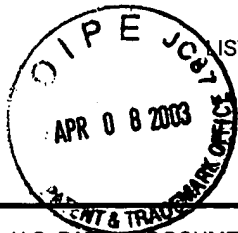
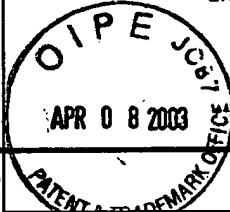


Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1674	SERIAL NO. 09/920,978		
<div style="text-align: center;">  </div> <p style="text-align: center;">LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)</p>				APPLICANT: Shane J. Trapp			
				FILING DATE August 1, 2001	GROUP 2813		
U.S. PATENT DOCUMENTS							
*Examiner's Initials	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
DS	AA	4,985,373	01/15/91	Levinstein et al.			
DS	AB	6,103,137	08/15/00	Park			
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AJ						
	AK						
	AL						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
DS	AM	Smolinsky et al., <i>Reactive Ion Etching of Silicon Oxides with ammonia and Trifluoromethane. The Role of ...</i> , J. ELECTROCHEM. SOC.: SOLID-STATE SCIENCE AND TECHNOLOGY, pp. 1036-1039 (May 1982).					
	AN	Wolf, <i>SILICON PROCESSING FOR THE VLSI ERA, VOLUME 2: PROCESS INTEGRATION</i> , pp. 52-54 plus title pages (Lattice Press 1990). <i>Previously listed on pro 892 paper #8</i>					
	AO						
EXAMINER: <i>DS</i>		DATE CONSIDERED: 4/25/03					
<p><small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small></p>							


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U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
Previously considered	AA	5,863,827	01/26/99	Joyner	438	425	
	AB	5,883,006	03/16/99	Iba	438	712	
	AC	5,888,880	03/30/99	Gardner et al.	438	424	
	AD	5,895,253	04/20/99	Akram	438	424	
	AE	5,904,540	05/18/99	Sheng et al.	438	427	
	AF	5,930,645	07/27/99	Lyons et al.	438	424	
	AG	5,943,585	08/24/99	May et al.	438	400	
	AH	5,950,084	09/07/99	Lin et al.	438	400	
	AI	5,960,299	09/28/99	Yew et al.	438	424	
	AJ	5,972,773	10/26/99	Liu et al.	438	424	
AK	5,998,280	12/07/99	Bergemont et al.	438	425		

FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AL							
AM							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
Previously considered	AN	Kiermasz et al., Planarization for Sub-Micron Devices Utilising a New Chemistry, Electrotech, Presented at DUMIC Conference, California (February 1995).
	AO	Matsuura et al., A Highly Reliable Self-planarizing Low-k Intermetal Dielectric for Sub-quarter Micron Interconnects, IEEE 785-788 (1997).
Previously considered	AP	Matsuura et al., Novel Self-planarizing CVD Oxide for Interlayer Dielectric Applications, IEEE 117-120 (1994).

EXAMINER 	DATE CONSIDERED 4/25/03
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